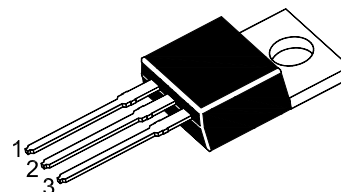


# ST BD910 / ST BD912

## PNP Complementary Silicon Power Transistors

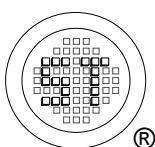


1.Base 2.Collector 3.Emitter

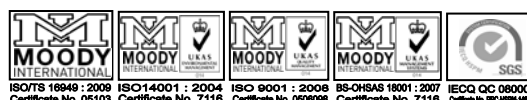
TO-220 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value		Unit
		ST BD910	ST BD912	
Collector Base Voltage	$-V_{CBO}$	80	100	V
Collector Emitter Voltage	$-V_{CEO}$	80	100	V
Emitter Base Voltage	$-V_{EBO}$	5		V
Collector Current	$-I_C$	15		A
Base Current	$-I_B$	5		A
Total Power Dissipation @ $T_C \leq 25\text{ }^\circ\text{C}$	$P_{tot}$	90		W
Operating Junction Temperature Range	$T_J$	150		$^\circ\text{C}$
Storage Junction Temperature Range	$T_J, T_s$	-65 to +150		$^\circ\text{C}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.4		$^\circ\text{C/W}$



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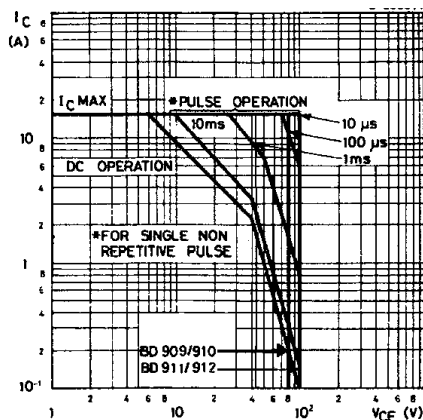
Dated : 22/03/2006

# ST BD910 / ST BD912

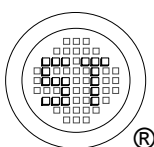
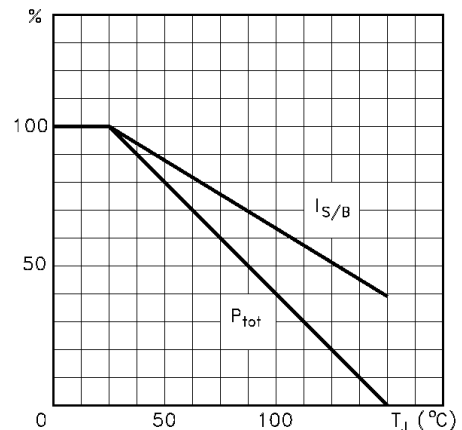
## Characteristics at $T_c = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain					
at $-V_{CE} = 4\text{ V}$ , $-I_C = 0.5\text{ A}$	$h_{FE}$	40	250	-	
at $-V_{CE} = 4\text{ V}$ , $-I_C = 5\text{ A}$	$h_{FE}$	15	150	-	
at $-V_{CE} = 4\text{ V}$ , $-I_C = 10\text{ A}$	$h_{FE}$	5	-	-	
Collector Emitter Sustaining Voltage					
at $-I_C = 100\text{ mA}$	ST BD910 ST BD912	$-V_{CEO(sus)}$	80 100	- -	V
Collector Cutoff Current					
at $-V_{CB} = 80\text{ V}$	ST BD910	$-I_{CBO}$	-	0.5	mA
at $-V_{CB} = 100\text{ V}$	ST BD912	$-I_{CBO}$	-	0.5	mA
Collector Cutoff Current					
at $-V_{CE} = 40\text{ V}$	ST BD910	$-I_{CEO}$	-	1	mA
at $-V_{CE} = 50\text{ V}$	ST BD912	$-I_{CEO}$	-	1	mA
Emitter Cutoff Current					
at $-V_{EB} = 5\text{ V}$		$-I_{EBO}$	-	1	mA
Collector Emitter Saturation Voltage					
at $-I_C = 5\text{ A}$ , $-I_B = 0.5\text{ A}$		$-V_{CE(sat)}$	-	1	V
at $-I_C = 10\text{ A}$ , $-I_B = 2.5\text{ A}$		$-V_{CE(sat)}$	-	3	V
Base Emitter Saturation Voltage					
at $-I_C = 10\text{ A}$ , $-I_B = 2.5\text{ A}$		$-V_{BE(sat)}$	-	2.5	V
Base Emitter Voltage					
at $-I_C = 5\text{ A}$ , $-V_{CE} = 4\text{ V}$		$-V_{BE}$	-	1.5	V
Transition Frequency					
at $-V_{CE} = 4\text{ V}$ , $-I_C = 0.5\text{ A}$ ,		$f_T$	3	-	MHz

Safe Operating Area



Derating Curves

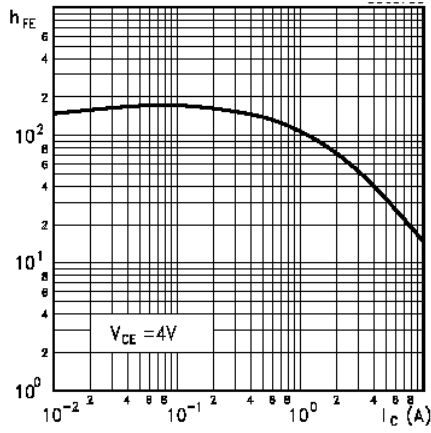


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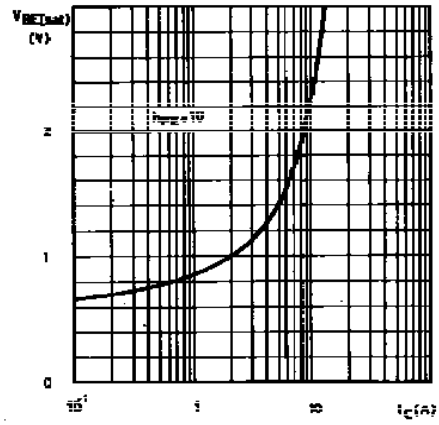


# ST BD910 / ST BD912

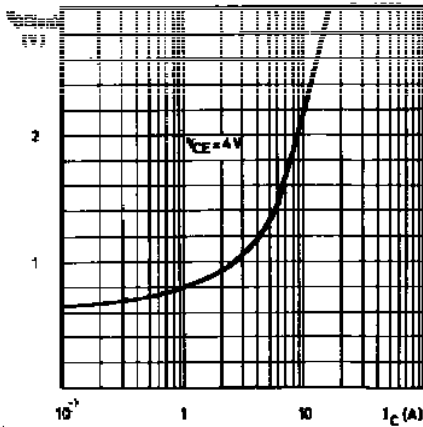
DC Current Gain



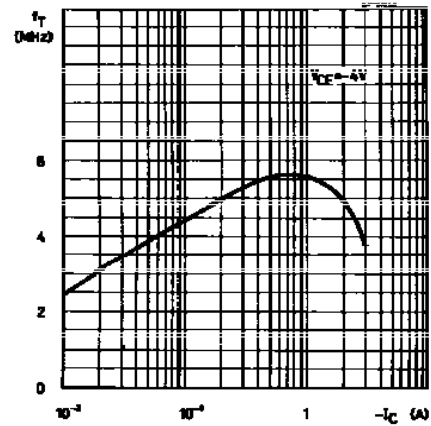
Base-Emitter Saturation Voltage



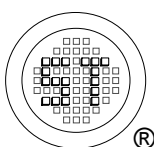
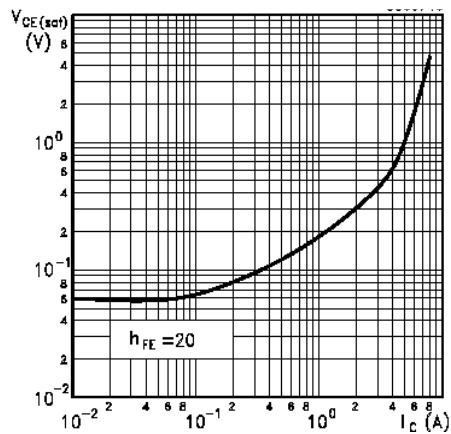
DC Transconductance



Transition Frequency



Collector-Emitter Saturation Voltage

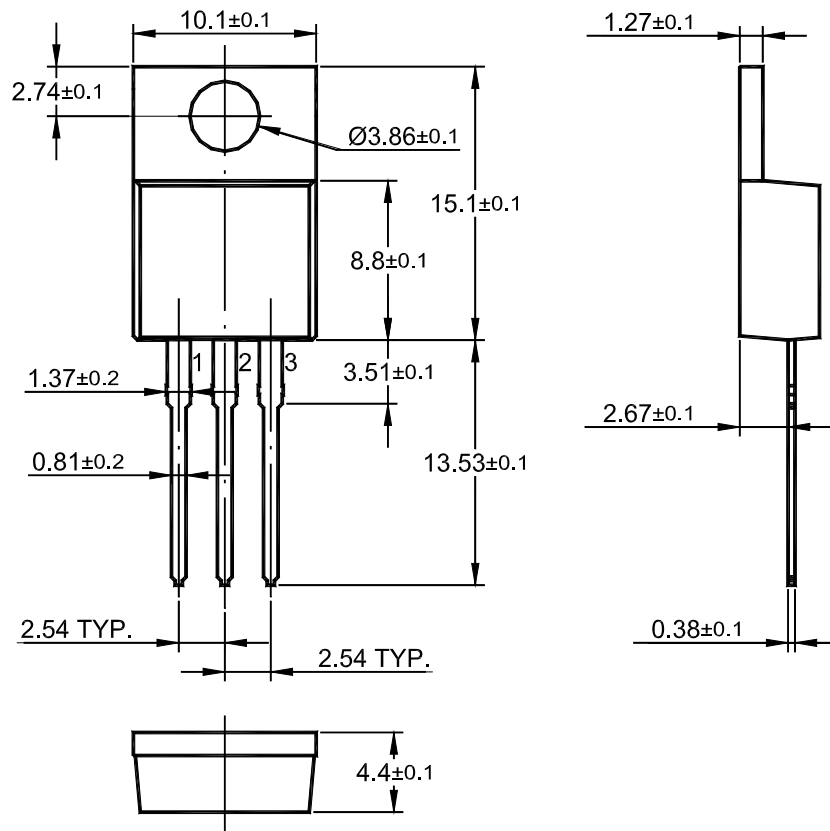


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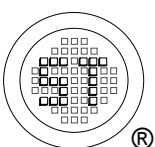


# ST BD910 / ST BD912

## TO-220 PACKAGE OUTLINE



Dimensions in mm



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